

IN THE CLAIMS:

Please amend the claims as follows:

15. (Third Amendment) A method of manufacturing a semiconductor device, comprising steps of:
forming at least one semiconductor island over a substrate;
spinning the substrate;
contacting an etching solution to a surface of said semiconductor island and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surface; and then forming a gate insulating film over said semiconductor island after the contaminating impurities are removed from the surfaces.

19. (Third Amendment) A method of manufacturing a semiconductor device, comprising steps of:
forming a semiconductor film over a substrate;
crystallizing said semiconductor film;
forming at least one semiconductor island over said substrate by patterning the crystallized semiconductor film ;
spinning the substrate;
contacting an etching solution to a surface of said semiconductor island and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surface; and then forming a gate insulating film over said semiconductor island after the contaminating impurities are removed from the surfaces; and
forming a gate electrode over said gate insulating film.

23. (Third Amendment) A method of manufacturing a semiconductor device, comprising steps of:

- forming gate wirings over a substrate;
- spinning the substrate;
- contacting an etching solution to surfaces of said substrate and said gate wirings and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surfaces; and then
- forming a gate insulating film and a semiconductor film over said gate wirings after the contaminating impurities are removed from the surfaces.

27. (Twice Amended) A method of manufacturing a semiconductor device, comprising steps of:

- forming gate wirings over a substrate;
- spinning the substrate;
- contacting an etching solution to surfaces of said substrate and said gate wirings and scattering the etching solution during said spinning, thereby contaminating impurities are removed from the surfaces; and then
- forming a gate insulating film and a semiconductor film over said gate wirings, continuously after the contaminating impurities are removed from the surfaces.